

PSMN057-200B

N-channel TrenchMOS SiliconMAX standard level FET 15 August 2013 Product data sheet

1. General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

2. Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

3. Applications

- DC-to-DC converters
- Switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	200	V
I _D	drain current	T _{mb} = 25 °C		-	-	39	Α
P _{tot}	total power dissipation			-	-	250	W
Static charact	eristics						,
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 17 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	41	57	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 39 A; V_{DS} = 160 V; T_j = 25 °C		-	37	50	nC



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain		
3	S	source		G TITA
mb	D	mounting base; connected to drain	1 3	mbb076 S
			D2PAK (SOT404)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN057-200B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN057-200B	PSMN057-200B

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	200	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	200	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 100 °C	-	27.5	Α
		T _{mb} = 25 °C	-	39	Α
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C	-	156	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	250	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
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Symbol	Parameter	Conditions	Min	Max	Unit
Source-dra	in diode				
I _S	source current	T _{mb} = 25 °C	-	39	Α
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	156	Α
Avalanche	ruggedness		l		
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 35 A; $V_{sup} \le 50$ V; unclamped; t_p = 100 μs; R_{GS} = 50 Ω	-	300	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 50$ V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; R_{GS} = 50 Ω; unclamped	-	35	A

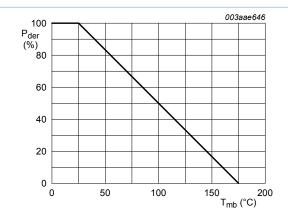


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

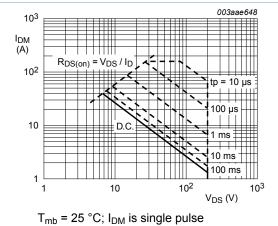


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

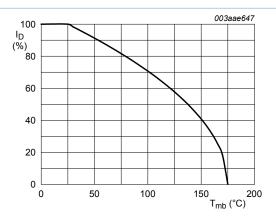
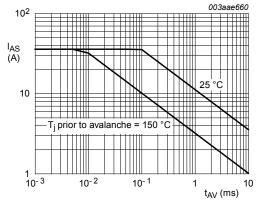


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$



unclamped inductive load

 ig. 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	0.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	50	-	K/W

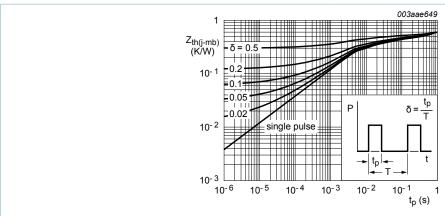


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	acteristics		, , , , , , , , , , , , , , , , , , ,				
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	200	-	-	V	
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	178	-	-	V	
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	4.4	V	
I _{DSS} drain leakag	I _{DSS}	drain leakage current	V _{DS} = 200 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V _{DS} = 200 V; V _{GS} = 0 V; T _j = 25 °C	-	0.03	10	μA	
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA	
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 17 A; T _j = 175 °C	-	-	165	mΩ	
	resistance	V _{GS} = 10 V; I _D = 17 A; T _j = 25 °C	-	41	57	mΩ	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R_G	internal gate resistance (AC)	f = 1 MHz	-	2	4.1	Ω
Dynamic ch	naracteristics				'	,
Q _{G(tot)}	total gate charge	I _D = 39 A; V _{DS} = 160 V; V _{GS} = 10 V;	-	96	135	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	13	-	nC
Q_{GD}	gate-drain charge		-	37	50	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	3750	5036	pF
C _{oss}	output capacitance		-	385	520	pF
C _{rss}	reverse transfer capacitance		-	180	252	pF
t _{d(on)}	turn-on delay time	V_{DS} = 100 V; R_L = 2.7 Ω ; V_{GS} = 10 V;	-	18	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 °C$	-	58	-	ns
t _{d(off)}	turn-off delay time		-	105	-	ns
t _f	fall time		-	78	-	ns
L _D	internal drain inductance	measured from tab to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	3.5	-	nΗ
L _S	internal source inductance	measured from source lead to source bond pad; $T_j = 25$ °C	-	7.5	-	nH
Source-dra	in diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	133	173	ns
Q _r	recovered charge	$V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	895	-	nC

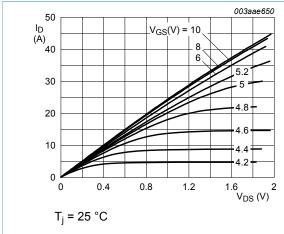


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

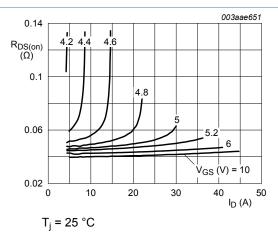


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values

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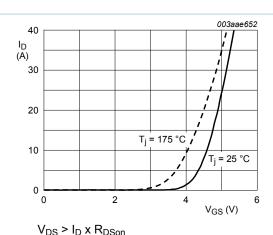


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

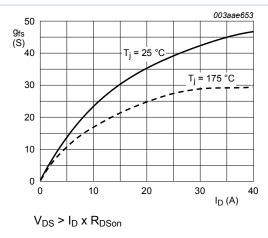


Fig. 9. Forward transconductance as a function of drain current; typical values

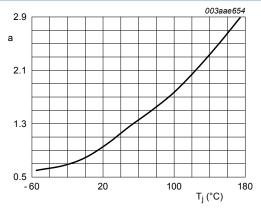


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature

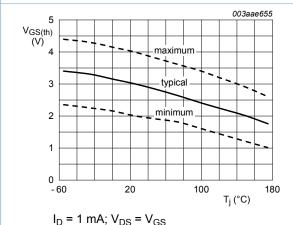


Fig. 11. Gate-source threshold voltage as a function of junction temperature



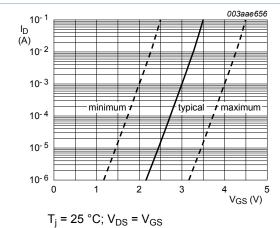
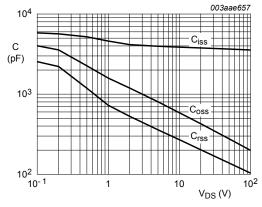


Fig. 12. Sub-threshold drain current as a function of gate-source voltage



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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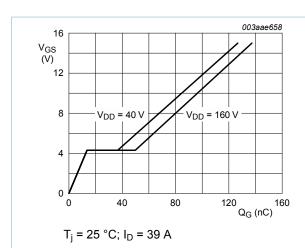


Fig. 14. Gate-source voltage as a function of gate charge; typical values

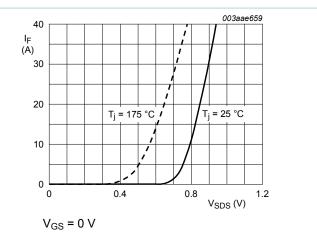
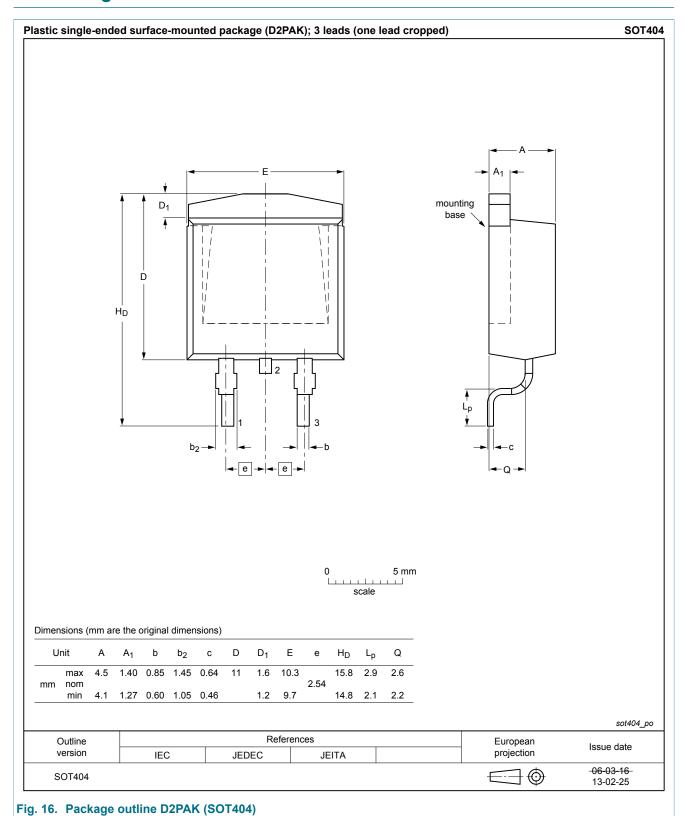


Fig. 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

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11. Package outline



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